# 2N3766 2N3767

# SILICON NPN POWER TRANSISTORS



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# **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N3766 and 2N3767 are silicon NPN power transistors manufactured by the epitaxial base process designed for power amplifier and medium speed switching applications.





MAXIMUM F Collector-Ba	RATINGS: (T <sub>C</sub> =25°C) se Voltage	SYMBOL V <sub>CBO</sub>	<b>2N3766</b> 80	<b>2N3767</b> 100	UNITS V
Collector-Em	nitter Voltage	$V_{CEO}$	60	80	V
Emitter-Base Voltage		$V_{EBO}$	6.0		V
Continuous Collector Current		$I_{\mathbb{C}}$	4.0		Α
Continuous Base Current		$I_{B}$	2.0		Α
Power Dissipation		$P_{D}$	25		W
Operating and Storage Junction Temperature		T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C
Thermal Resistance		ΘJC	7.0		°C/W
ELECTRICA	L CHARACTERISTICS: (T <sub>C</sub> =25°C ι	unless otherwise	noted)		
SYMBOL	TEST CONDITIONS	MIN	M	ΑX	UNITS
I <sub>CBO</sub>	V <sub>CB</sub> =Rated V <sub>CBO</sub>		1	0	μΑ
I <sub>CEV</sub>	$V_{CE}$ =Rated $V_{CEO}$ , $V_{EB}$ =1.5 $V$		1	0	μΑ
ICEO	V <sub>CF</sub> =Rated V <sub>CFO</sub>		50	00	μA

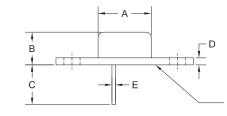
			UNITS
V <sub>CB</sub> =Rated V <sub>CBO</sub>	191114	10	μΑ
V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>EB</sub> =1.5V		10	μΑ
V <sub>CE</sub> =Rated V <sub>CEO</sub>		500	μΑ
V <sub>EB</sub> =6.0V		500	μΑ
I <sub>C</sub> =100mA (2N3766)	60		V
I <sub>C</sub> =100mA (2N3767)	80		V
I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		1.0	V
I <sub>C</sub> =1.0A, I <sub>B</sub> =100mA		2.5	V
$V_{CE}$ 10V, $I_{C}$ =1.0A		1.5	V
$V_{CE}$ =5.0V, $I_{C}$ =50mA	30		
$V_{CE}$ =5.0V, $I_{C}$ =500mA	40	160	
$V_{CE}$ =10V, $I_{C}$ =1.0A	20		
$V_{CE}$ =10V, $I_{C}$ =500mA, f=10MHz	10		MHz
$V_{CB}$ =10V, $I_E$ =0, f=100kHz		50	pF
	TEST CONDITIONS  V <sub>CB</sub> =Rated V <sub>CBO</sub> V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>EB</sub> =1.5V  V <sub>CE</sub> =Rated V <sub>CEO</sub> V <sub>EB</sub> =6.0V  I <sub>C</sub> =100mA (2N3766)  I <sub>C</sub> =100mA (2N3767)  I <sub>C</sub> =500mA, I <sub>B</sub> =50mA  I <sub>C</sub> =1.0A, I <sub>B</sub> =100mA  V <sub>CE</sub> =1.0A, I <sub>C</sub> =500mA  V <sub>CE</sub> =5.0V, I <sub>C</sub> =500mA  V <sub>CE</sub> =10V, I <sub>C</sub> =1.0A  V <sub>CE</sub> =10V, I <sub>C</sub> =500mA, f=10MHz	TEST CONDITIONS  V <sub>CB</sub> =Rated V <sub>CBO</sub> V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>EB</sub> =1.5V  V <sub>CE</sub> =Rated V <sub>CEO</sub> V <sub>EB</sub> =6.0V  I <sub>C</sub> =100mA (2N3766) 60  I <sub>C</sub> =100mA (2N3767) 80  I <sub>C</sub> =500mA, I <sub>B</sub> =50mA  I <sub>C</sub> =1.0A, I <sub>B</sub> =100mA  V <sub>CE</sub> 10V, I <sub>C</sub> =1.0A  V <sub>CE</sub> =5.0V, I <sub>C</sub> =50mA 30  V <sub>CE</sub> =5.0V, I <sub>C</sub> =500mA 40  V <sub>CE</sub> =10V, I <sub>C</sub> =1.0A 20  V <sub>CE</sub> =10V, I <sub>C</sub> =500mA, f=10MHz 10	VCB=Rated VCBO       10         VCE=Rated VCEO, VEB=1.5V       10         VCE=Rated VCEO       500         VEB=6.0V       500         IC=100mA (2N3766)       60         IC=100mA (2N3767)       80         IC=500mA, IB=50mA       1.0         IC=1.0A, IB=100mA       2.5         VCE10V, IC=1.0A       1.5         VCE=5.0V, IC=50mA       30         VCE=5.0V, IC=500mA       40       160         VCE=10V, IC=1.0A       20         VCE=10V, IC=500mA, f=10MHz       10

# 2N3766 2N3767

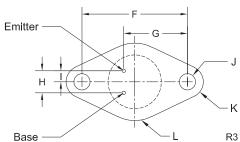
# SILICON NPN POWER TRANSISTORS



# **TO-66 CASE - MECHANICAL OUTLINE**



Seating Plane: The seating plane must be within 0.001" concave to 0.004" convex within 0.600" diameter from the center of the device.



MARKING: FULL PART NUMBER

DIMENSIONS								
	INCHES		MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
A (DIA)	0.470	0.500	11.94	12.70				
В	0.250	0.340	6.35	8.64				
С	0.360	-	9.14	-				
D	0.050	0.075	1.27	1.91				
E (DIA)	0.028	0.034	0.71	0.86				
F	0.956	0.964	24.28	24.48				
G	0.570	0.590	14.48	14.99				
Н	0.190	0.210	4.83	5.33				
I	0.093	0.107	2.36	2.72				
J (DIA)	0.142	0.152	3.61	3.86				
K (RAD)	0.141		3.58					
L (RAD)	0.345		8.76					

TO-66 (REV:R3)

## **OUTSTANDING SUPPORT AND SUPERIOR SERVICES**



#### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

#### **DESIGNER SUPPORT/SERVICES**

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- Custom product and package development

## REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

### **CONTACT US**

## Corporate Headquarters & Customer Support Team

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